

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

MSESD0522P

Product specification

Features

- 150Watts peak pulse power ($t_p = 8/20\mu s$)
- SLP1610-4 package
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance ($C_j = 0.3pF$ typ. IO to IO)
- Protection one data/power line to:
- IEC 61000-4-2 $\pm 15kV$ contact $\pm 20kV$ air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 4A (8/20 μs)

Mechanical Data

- SLP1610-4 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

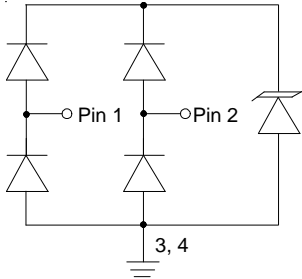
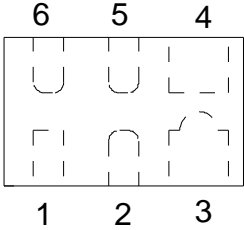
Applications

- Digital Visual Interface (DVI)
- MDDI Ports
- PCI Express
- eSATA Interface

Reference News

SLP1610-4	Marking
	

Schematic & PIN Configuration

 <p>Schematic</p>	 <p>SLP1610-4</p>
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Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power ($t_p = 8/20\mu s$)	P_{PP}	150	Watts
Peak Pulse Current ($t_p = 8/20\mu s$) (note1)	I_{PP}	4.0	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V_{ESD}	20 15	kV
Lead Soldering Temperature	T_L	260(10seconds)	$^{\circ}C$
Junction Temperature	T_J	-55 to + 125	$^{\circ}C$
Storage Temperature	T_{stg}	-55 to + 125	$^{\circ}C$

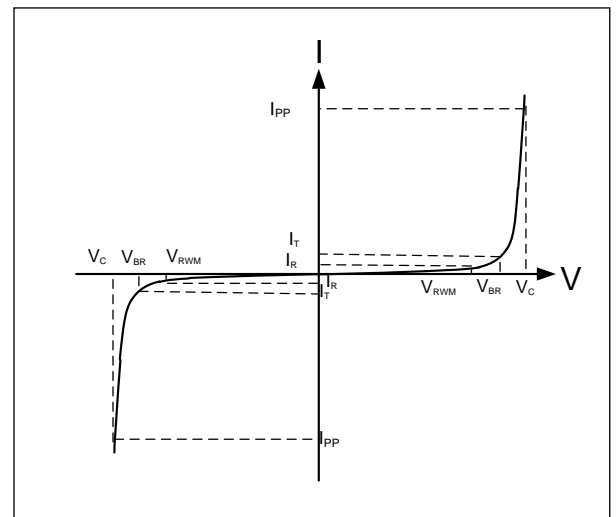
Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{RWM}				5.0	V
Reverse Breakdown Voltage	V_{BR}	$I_T = 1mA$	6.0			V
Reverse Leakage Current	I_R	$V_{RWM} = 5V, T = 25^{\circ}C$			1.0	μA
Peak Pulse Current	I_{PP}	$t_p = 8/20\mu s$			4.0	A
Clamping Voltage	V_C	$I_{PP} = 1A, t_p = 8/20\mu s$			15	V
Junction Capacitance	C_j	IO to IO $V_R = 0V, f = 1MHz$		0.3	0.5	pF

Electrical Parameters (TA = 25°C unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current

Note: 8/20 μs pulse waveform.



Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

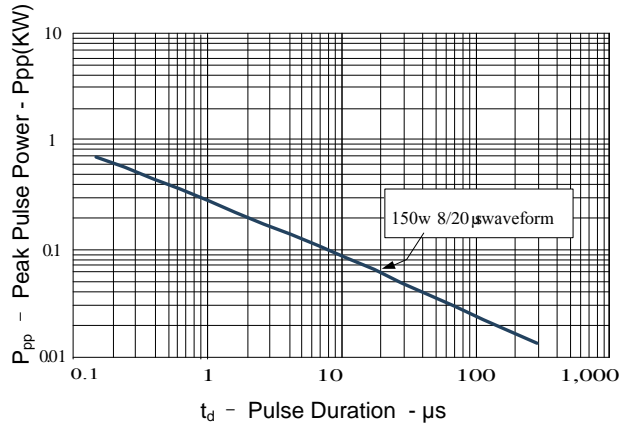


Figure 2: Power Derating Curve

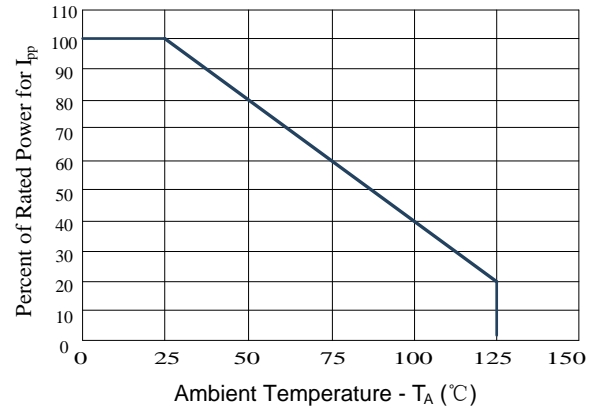


Figure3: Pulse Waveform

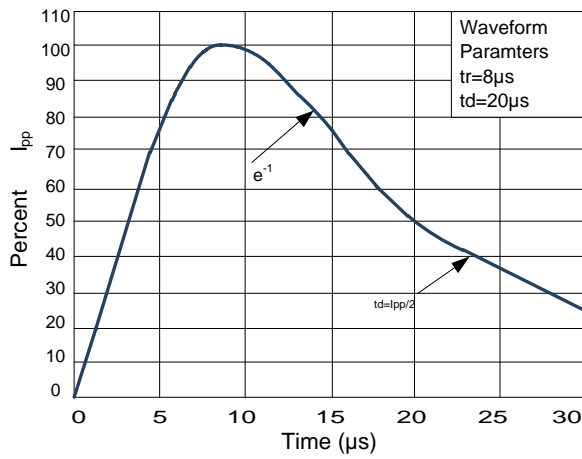
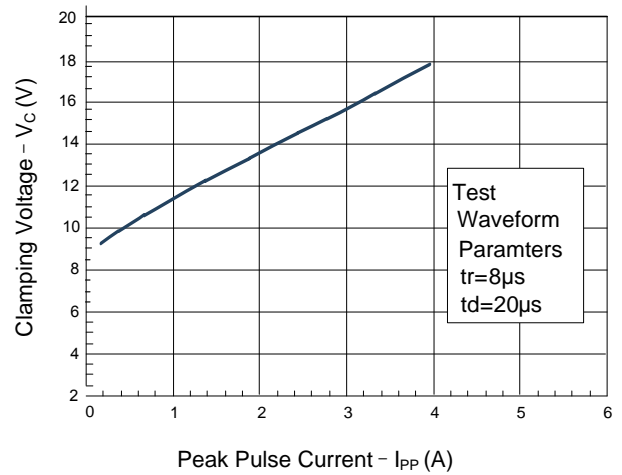
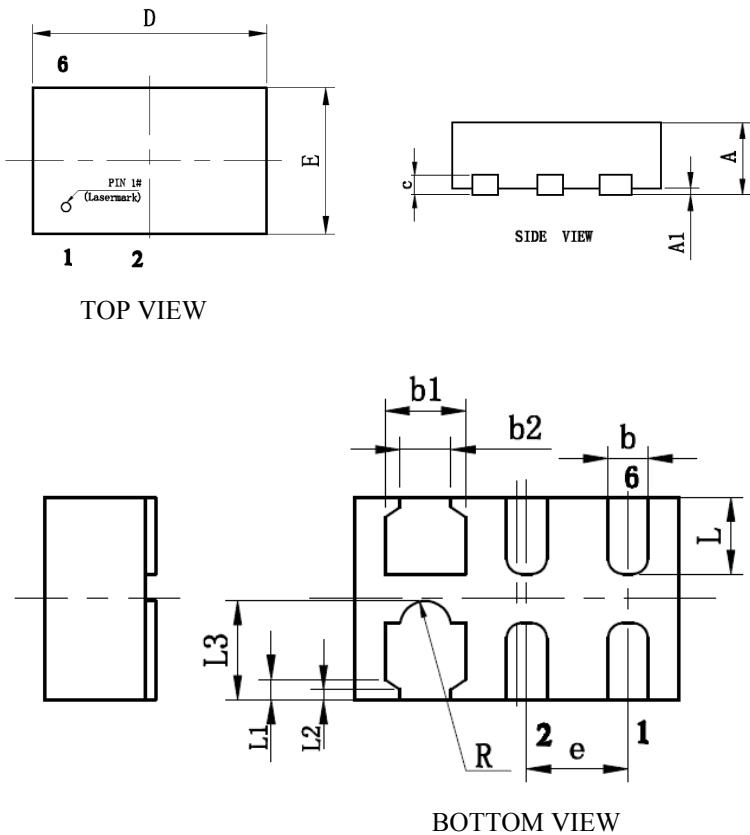


Figure 4: Clamping Voltage vs. Ipp



Outline Drawing



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.50	0.55	0.60
A1	—	0.02	0.05
b	0.15	0.20	0.25
b1	0.35	0.40	0.45
b2	0.20	0.25	0.30
c	0.10	0.15	0.20
D	1.55	1.60	1.65
e	0.50BSC		
E	0.95	1.00	1.05
L	0.33	0.38	0.43
L1	0.100REF		
L2	0.05REF		
L3	0.49REF		
R	0.08	0.13	0.18

Order information

Orderable Device	Package	Packing Option
MSESD0522P	SLP1610-4	3000PCS

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